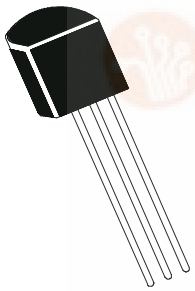
Continental Device India Limited
An IS/ISO 9002 and IECQ Certified Manufacturer

IS/ISO 9002
Lic# QSC/L- 000019.2

NPN COMPLEMENTARY SILICON HIGH VOLTAGE TRANSISTOR

CC5551
(9AW)
TO-92
BCE



MARKING : NCC 5551

High Voltage NPN Transistor for General Purpose and Telephony Applications

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector -Emitter Voltage	V_{CEO}	160	V
Collector -Base Voltage	V_{CBO}	180	V
Emitter -Base Voltage	V_{EBO}	6.0	V
Collector Current Continuous	I_C	600	mA
Power Dissipation @Ta=25°C	P_D	625	mW
Derate Above 25°C		5.0	mw/°C
Power Dissipation @Tc=25°C	P_D	1.5	W
Derate Above 25°C		12	mw/°C
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C
THERMAL RESISTANCE			
Junction to Case	$R_{th(j-c)}$	125	°C/W
Junction to Ambient	$R_{th(j-a)}$ (1)	357	°C/W

(1) $R_{th(j-a)}$ is measured with the device soldered into a typical printed circuit board

ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector -Emitter Voltage	V_{CEO}	I_C=1mA,I_B=0	160	-	-	V
Collector -Base Voltage	V_{CBO}	I_C=100µA.I_E=0	180	-	-	V
Emitter -Base Voltage	V_{EBO}	I_E=10µA, I_C=-0	6.0	-	-	V
Collector-Cut off Current	I_{CBO}	V_{CB}=160V, I_E=0	-	-	50	nA
		T_a=100°C				
		V_{CB}=160V, I_E=0	-	-	50	µA
Emitter-Cut off Current	I_{EBO}	V_{EB}=4V, I_C=0	-	-	50	nA
DC Current Gain	h_{FE*}	I_C=1mA,V_{CE}=5V	80	-	-	
		I_C=10mA,V_{CE}=5V	80	-	320	
		I_C=50mA,V_{CE}=5V	30	-	-	
Collector Emitter Saturation Voltage	$V_{CE(Sat)*}$	I_C=10mA,I_B=1mA	-	-	0.15	V
		I_C=50mA,I_B=5mA	-	-	0.2	V
Base Emitter Saturation Voltage	$V_{BE(Sat)*}$	I_C=10mA,I_B=1mA	-	-	1.0	V
		I_C=50mA,I_B=5mA	-	-	1.0	V

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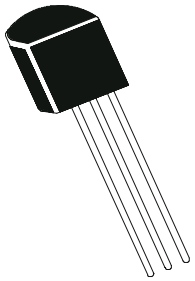

ELECTRICAL CHARACTERISTICS (Ta=25°C Unless Otherwise Specified) **CC5551**

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Dynamic Characteristics						
Small Signal Current Gain	h_{fe}	I_C=1mA, V_{CE}=10V f=1KHz	80	-	320	
Transition Frequency	f_t	V_{CE}=10V,I_C=10mA, f=100MHz	100	-	300	MHz
Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0 f=1MHz	-	-	6.0	pF
Input Capacitance	C_{ib}	V_{EB}=0.5V, I_C=0 f=1MHz	-	-	20	pF
Noise Figure	N_F	V_{CE}=5V, I_C=250μA R_S=1kΩ, f=10Hz to 15.7kHz	-	-	8.0	dB

***Pulse Test: Pulse Width=300us, Duty Cycle=2%**

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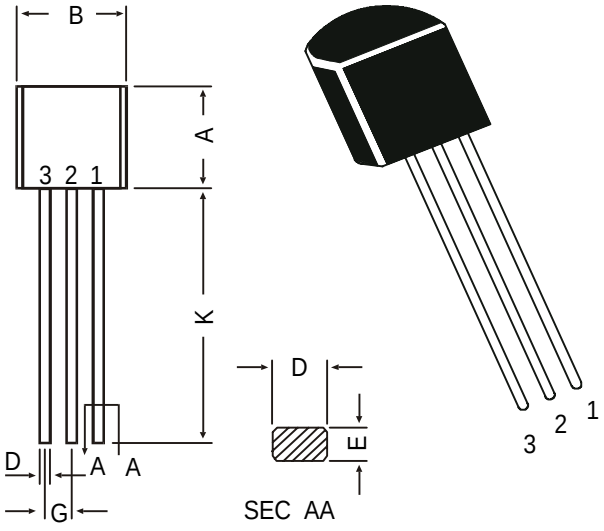
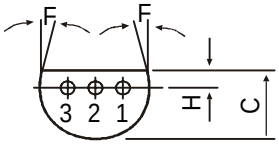
TO-92 Plastic Package





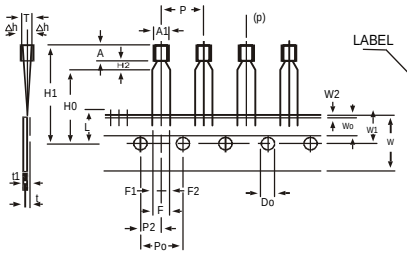
PIN CONFIGURATION
1. BASE
2. COLLECTOR
3. EMITTER

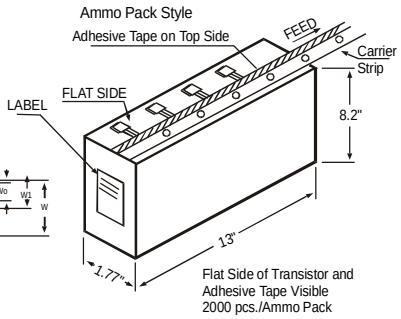
All diminsions in mm.

DIM	MIN.	MAX.
A	4.32	5.33
B	4.45	5.20
C	3.18	4.19
D	0.41	0.55
E	0.35	0.50
F	5 DEG	
G	1.14	1.40
H	1.14	1.53
K	12.70	—

TO-92 Transistors on Tape and Ammo Pack

MECHANICAL DATA





All dimensions in mm unless specified otherwise

ITEM	SYMBOL	SPECIFICATION MIN.	NOM.	MAX.	TOL .	REMARKS
BODY WIDTH	A1	4.0		4.8		
BODY HEIGHT	A	4.8		5.2		
BODY THICKNESS	T	3.9		4.2		
PITCH OF COMPONENT	P		12.7		±1	
FEED HOLE PITCH	Po		12.7		±0.3	CUMULATIVE PITCH ERROR 1.0 mm/20 PITCH
FEED HOLE CENTRE TO COMPONENT CENTRE	P2		6.35		±0.4	TO BE MEASURED AT BOTTOM OF CLINCH
DISTANCE BETWEEN OUTER LEADS	F		5.08		+0.6 -0.2	
COMPONENT ALIGNMENT	△h		0	1		AT TOP OF BODY
TAPE WIDTH	W		18		±0.5	
HOLD-DOWN TAPE WIDTH	Wo		6		±0.2	
HOLE POSITION	W1		9		+0.7 -0.5	
HOLD-DOWN TAPE POSITION	W2		0.5		±0.2	
LEAD WIRE CLINCH HEIGHT	Ho		16		±0.5	
COMPONENT HEIGHT	H1			23.25		
LENGTH OF SNIPPED LEADS	L			11.0		
FEED HOLE DIAMETER	Do		4		±0.2	
TOTAL TAPE THICKNESS	t			1.2		t1 0.3 - 0.6
LEAD - TO - LEAD DISTANCEF1,	F2		2.54		+0.4 -0.1	
CLINCH HEIGHT	H2			3		
PULL - OUT FORCE	(P)	6N				

NOTES
1. MAXIMUM ALIGNMENT DEVIATION BETWEEN LEADS NOT TO BE GREATER THAN 0.2 mm.
2. MAXIMUM NON-CUMULATIVE VARIATION BETWEEN TAPE FEED HOLES SHALL NOT EXCEED 1 mm IN 20 PITCHES.
3. HOLDDOWN TAPE NOT TO EXCEED BEYOND THE EDGE(S) OF CARRIER TAPE AND THERE SHALL BE NO EXPOSURE OF ADHESIVE.
4. NO MORE THAN 3 CONSECUTIVE MISSING COMPONENTS ARE PERMITTED.
5. A TAPE TRAILER, HAVING AT LEAST THREE FEED HOLES ARE REQUIRED AFTER THE LAST COMPONENT.
6. SPLICES SHALL NOT INTERFERE WITH THE SPROCKET FEED HOLES.

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-92 Bulk	1K/polybag	200 gm/1K pcs	3" x 7.5" x 7.5"	5.0K	17" x 15" x 13.5"	80.0K	23 kgs
TO-92 T&A	2K/ammo box	645 gm/2K pcs	12.5" x 8" x 1.8"	2.0K	17" x 15" x 13.5"	32.0K	12.5 kgs

Notes

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Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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